MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK31J60W

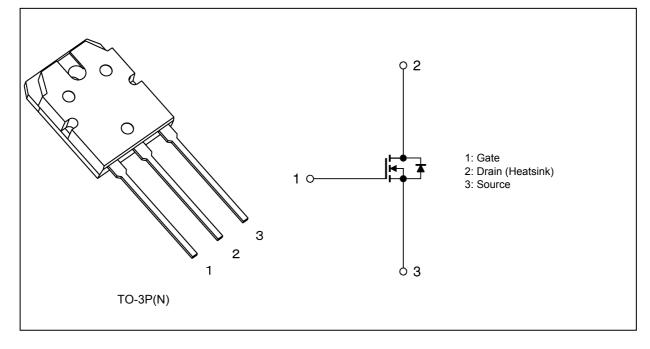
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.073 \Omega$ (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: V_{th} = 2.7 to 3.7 V ($V_{\rm DS}$ = 10 V, $I_{\rm D}$ = 1.5 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | | Symbol | Rating | Unit |
|-----------------------------------|----------|------------------|------------|-------|
| Drain-source voltage | | V _{DSS} | 600 | V |
| Gate-source voltage | | V _{GSS} | ±30 | 1 |
| Drain current (DC) | (Note 1) | I _D | 30.8 | A |
| Drain current (pulsed) | (Note 1) | I _{DP} | 123 | |
| Power dissipation (T _c | = 25°C) | PD | 230 | W |
| Single-pulse avalanche energy | (Note 2) | E _{AS} | 437 | mJ |
| Avalanche current | | I _{AR} | 7.7 | A |
| Reverse drain current (DC) | (Note 1) | I _{DR} | 30.8 | |
| Reverse drain current (pulsed) | (Note 1) | I _{DRP} | 123 | |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature | | T _{stg} | -55 to 150 |] |
| Mounting torque | | TOR | 0.8 | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 0.543 | °C/W |
| Channel-to-ambient thermal resistance | R _{th(ch-a)} | 50 | |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 12.9 mH, R_G = 25 Ω , I_{AR} = 7.7 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

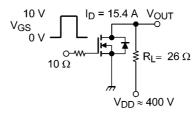
6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|-------------------------------------------------|-----|-------|-------|------|
| Gate leakage current | I _{GSS} | V_{GS} = ±30 V, V_{DS} = 0 V | _ | — | ±1 | μA |
| Drain cut-off current | I _{DSS} | V _{DS} = 600 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 600 | — | — | V |
| Gate threshold voltage | V _{th} | V _{DS} = 10 V, I _D = 1.5 mA | 2.7 | _ | 3.7 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 10 V, I _D = 15.4 A | | 0.073 | 0.088 | Ω |

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|--------------------|-------------------------------------------------------------|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz | _ | 3000 | _ | pF |
| Reverse transfer capacitance | C _{rss} |] | _ | 9.5 | _ | |
| Output capacitance | C _{oss} |] | _ | 70 | _ | |
| Effective output capacitance | C _{o(er)} | V_{DS} = 0 to 400 V, V_{GS} = 0 V | _ | 123 | _ | |
| Gate resistance | r _g | V _{DS} = OPEN, f = 1 MHz | _ | 2 | _ | Ω |
| Switching time (rise time) | t _r | See Figure 6.2.1 | _ | 32 | _ | ns |
| Switching time (turn-on time) | t _{on} |] | | 70 | | |
| Switching time (fall time) | t _f |] | _ | 8.5 | _ | |
| Switching time (turn-off time) | t _{off} | 1 | _ | 165 | _ | 1 |
| MOSFET dv/dt ruggedness | dv/dt | V _{DD} = 0 to 400 V, I _D = 7.7 A | 50 | _ | _ | V/ns |



Duty \leq 1%, t_w = 10 μ s

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------------------------|------------------|----------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 400 \text{ V}, V_{GS} \text{ = } 10 \text{V}, \text{I}_{D} \text{ = } 30.8 \text{A}$ | _ | 86 | — | nC |
| Gate-source charge 1 | Q _{gs1} | | _ | 18 | _ | |
| Gate-drain charge | Q _{gd} | | _ | 41 | _ | |

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------|------------------|-----------------------------------------------------|-----|------|------|------|
| Diode forward voltage | V _{DSF} | I _{DR} = 30.8 A, V _{GS} = 0 V | _ | _ | -1.7 | V |
| Reverse recovery time | t _{rr} | I _{DR} = 15.4 A, V _{GS} = 0 V | _ | 410 | _ | ns |
| Reverse recovery charge | Q _{rr} | -dI _{DR} /dt = 50 A/μs | _ | 3.5 | _ | μC |
| Peak reverse recovery current | I _{rr} | | _ | 17 | _ | А |
| Diode dv/dt ruggedness | dv/dt | I_{DR} = 15.4 A, V_{GS} = 0 V, V_{DD} = 400 V | 15 | _ | _ | V/ns |

7. Marking (Note)

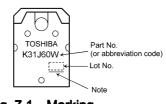


Fig. 7.1 Marking

 Note:
 A line under a Lot No. identifies the indication of product Labels.

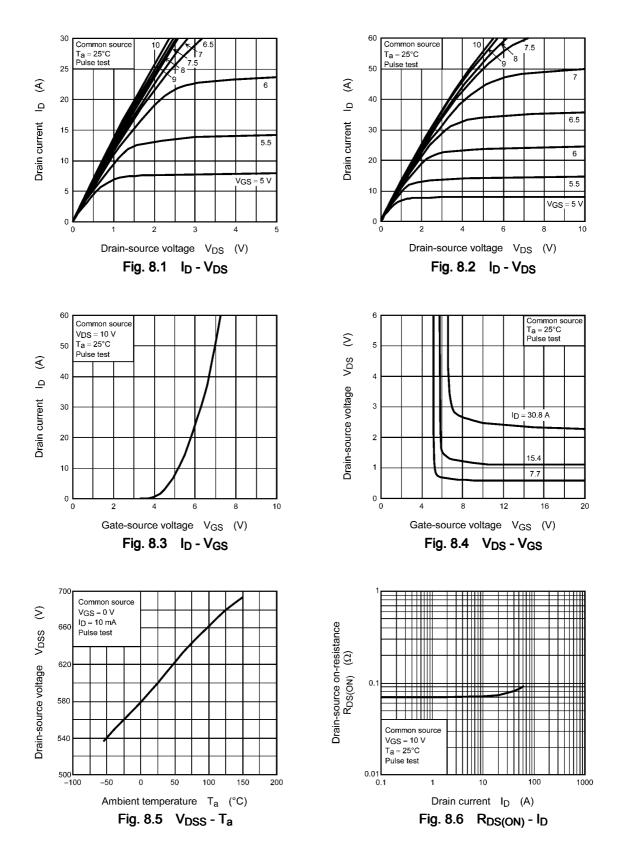
 Not underlined: [[Pb]]/INCLUDES > MCV

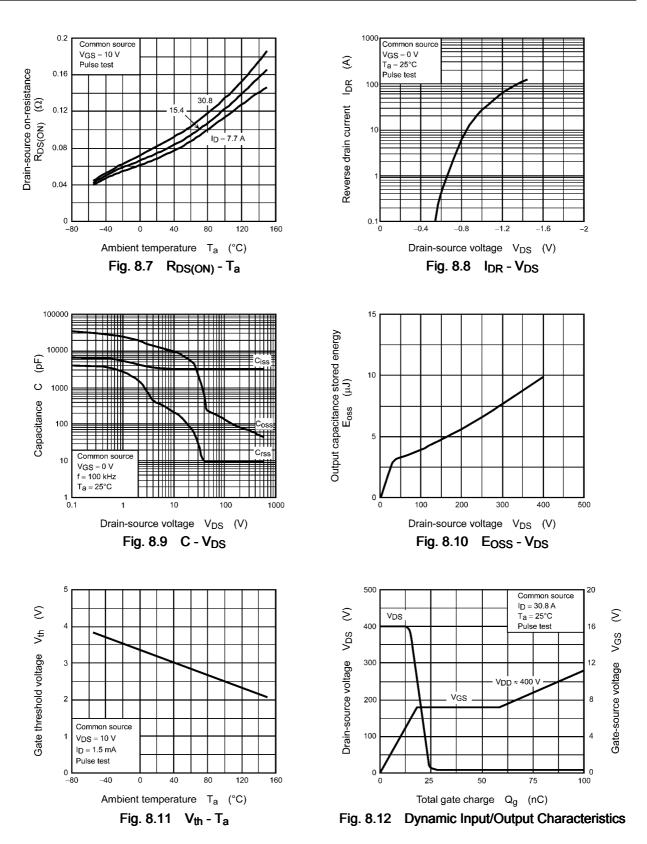
 Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

 Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

 The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)





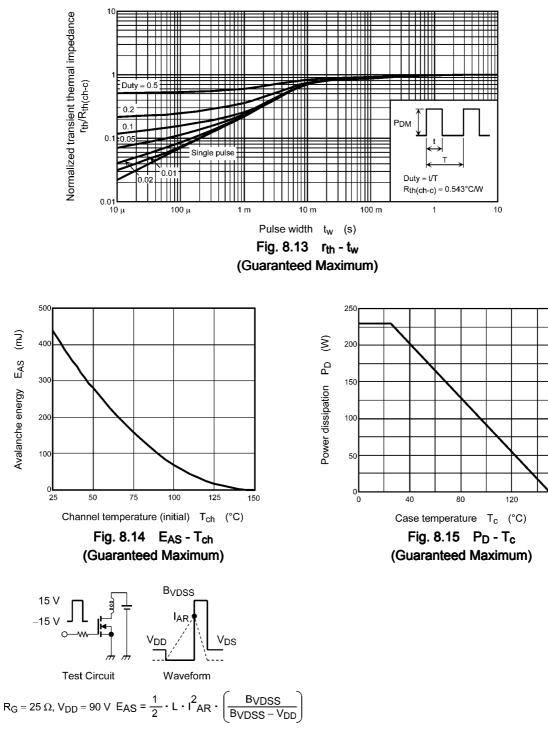
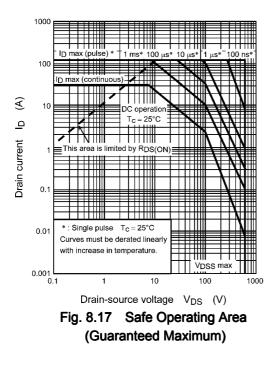


Fig. 8.16 Test Circuit/Waveform

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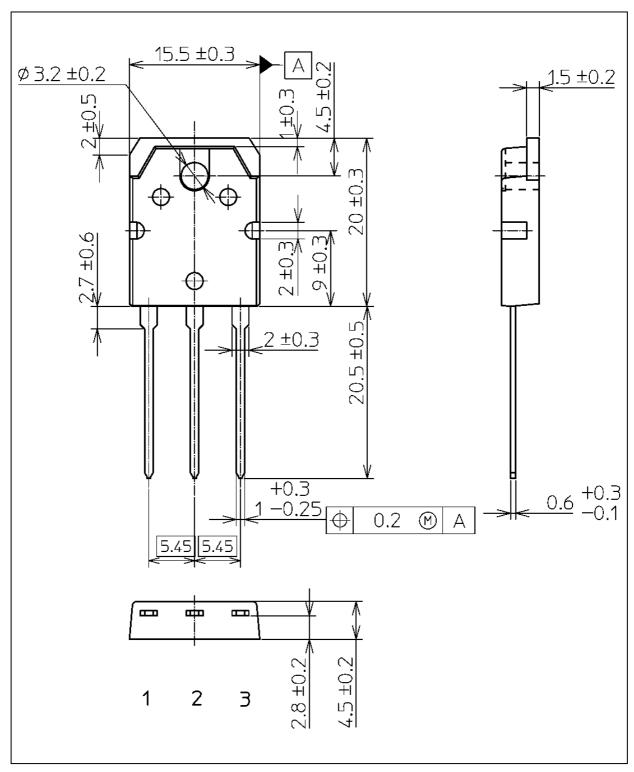


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

TK31J60W

Unit: mm



Weight: 4.6 g (typ.)

| Package Name(s) | |
|--------------------|--|
| JEITA: SC-65 | |
| TOSHIBA: 2-16C1S | |
| Nickname: TO-3P(N) | |

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